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(54) **METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE**

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H01J 37/32 (2006.01)

H01L 21/311 (2006.01)

H01L 21/768 (2006.01)

(52) **U.S. Cl.**

CPC **H01L 21/3065** (2013.01); **H01J 37/32082**
(2013.01); **H01J 37/32642** (2013.01);
H01L21/31116 (2013.01); **H01L 21/31122**
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21/76811 (2013.01); **H01L 21/76813** (2013.01)

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CPC H01L 21/31116; H01L 21/3065;
H01J 37/32082

USPC 438/710
See application file for complete search history.

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(57) **ABSTRACT**

A method of manufacturing a semiconductor device including a wafer using a plasma etching device which includes a chamber, a chuck provided in the chamber to dispose a wafer to be processed thereon, a focus ring disposed at a peripheral edge portion of the chuck, and a gas supplying mechanism configured to supply various types of gases depending a radial position of the wafer. The method includes: placing a wafer formed with an organic film on the chuck; introducing an etching gas which etches the organic film on the wafer from the process gas supplying mechanism to a central portion of the wafer; introducing an etching inhibiting factor gas having a property of reacting with the etching gas to the peripheral edge portion of the wafer from the gas supplying mechanism; and performing plasma etching on the wafer using the etching gas.

5 Claims, 12 Drawing Sheets

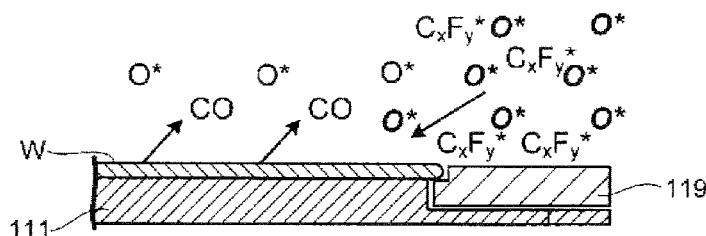
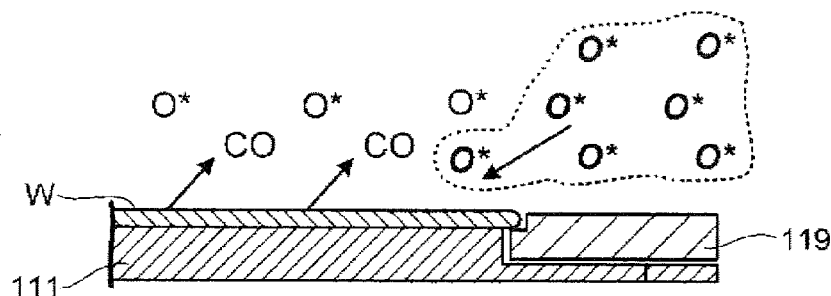
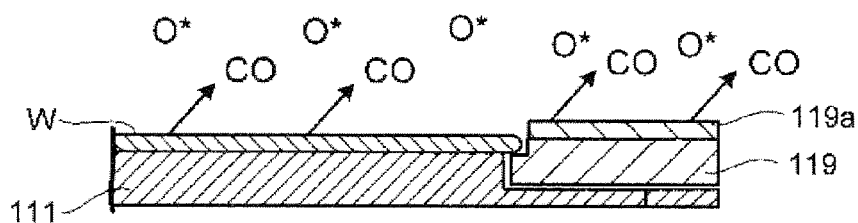
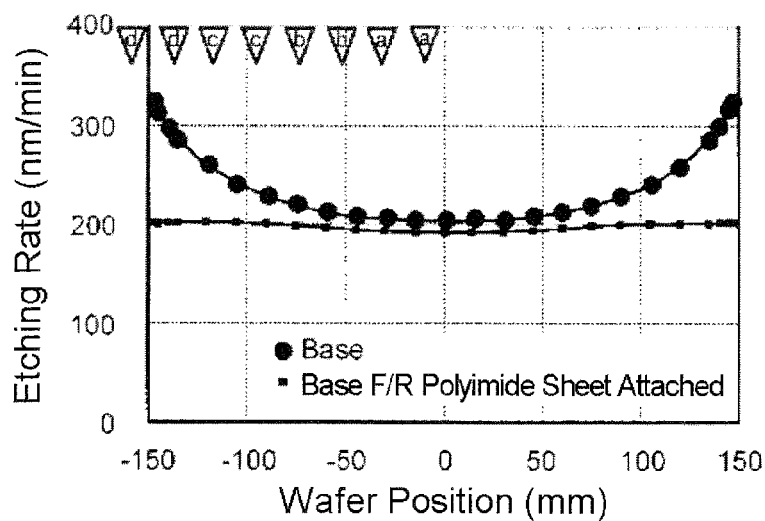


FIG.1A**FIG.1B****FIG.1C**

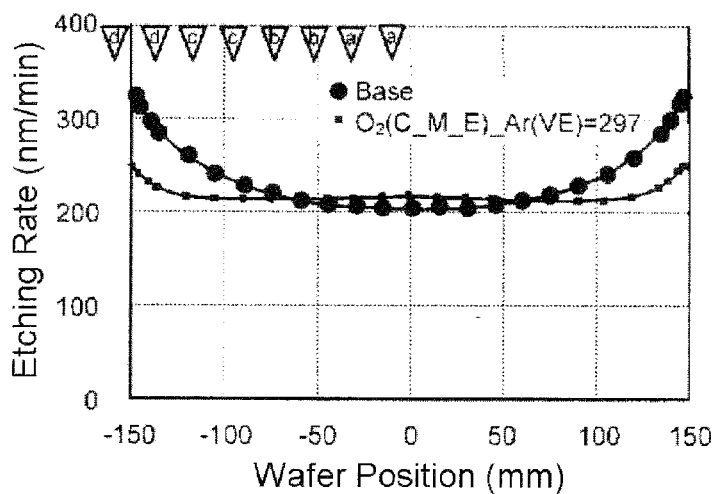
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Common: RDC=50, B.He(C/E)=30/40Torr, T/W/B=150/150/20deg.C

FIG.2A

List of Gas Flow Rate of Each Portion	Center (a)	Middle (b)	Edge (c)	Very Edge (d)
Base-O ₂ /Ar[sccm]	2.2/9.0	8.2/33	14.8/59	25/99

FIG.2B

List of Gas Flow Rate of Each Portion	Center (a)	Middle (b)	Edge (c)	Very Edge (d)
Current Base-O ₂ /Ar	4.3/9.0	16.3/33	29.3/59	0/297

FIG.2C

SOH condition: 10mT, 400+500W, DC=0V, O₂/Ar=50/200sccm, 58sec., (Ignition: 30mT, 2sec.)
Common: RDC=50, B.He(C/E)=30/40Torr, T/W/B=150/150/20deg.C

FIG. 3A

Gas Species of Each Portion	Center (a)	Middle (b)	Edge (c)	Very Edge (d)
Base	O_2/Ar	O_2/Ar	O_2/Ar	O_2/Ar
C_4F_6 added	O_2/Ar	O_2/Ar	O_2/Ar	C_4F_6

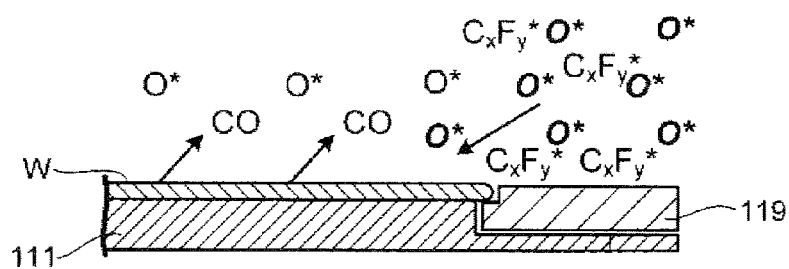
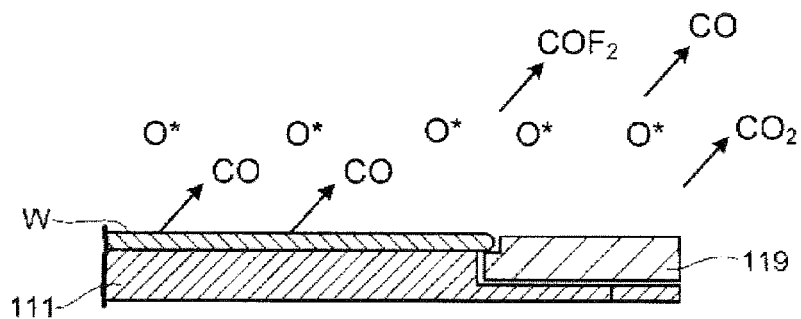
FIG. 3B**FIG. 3C**

FIG.4

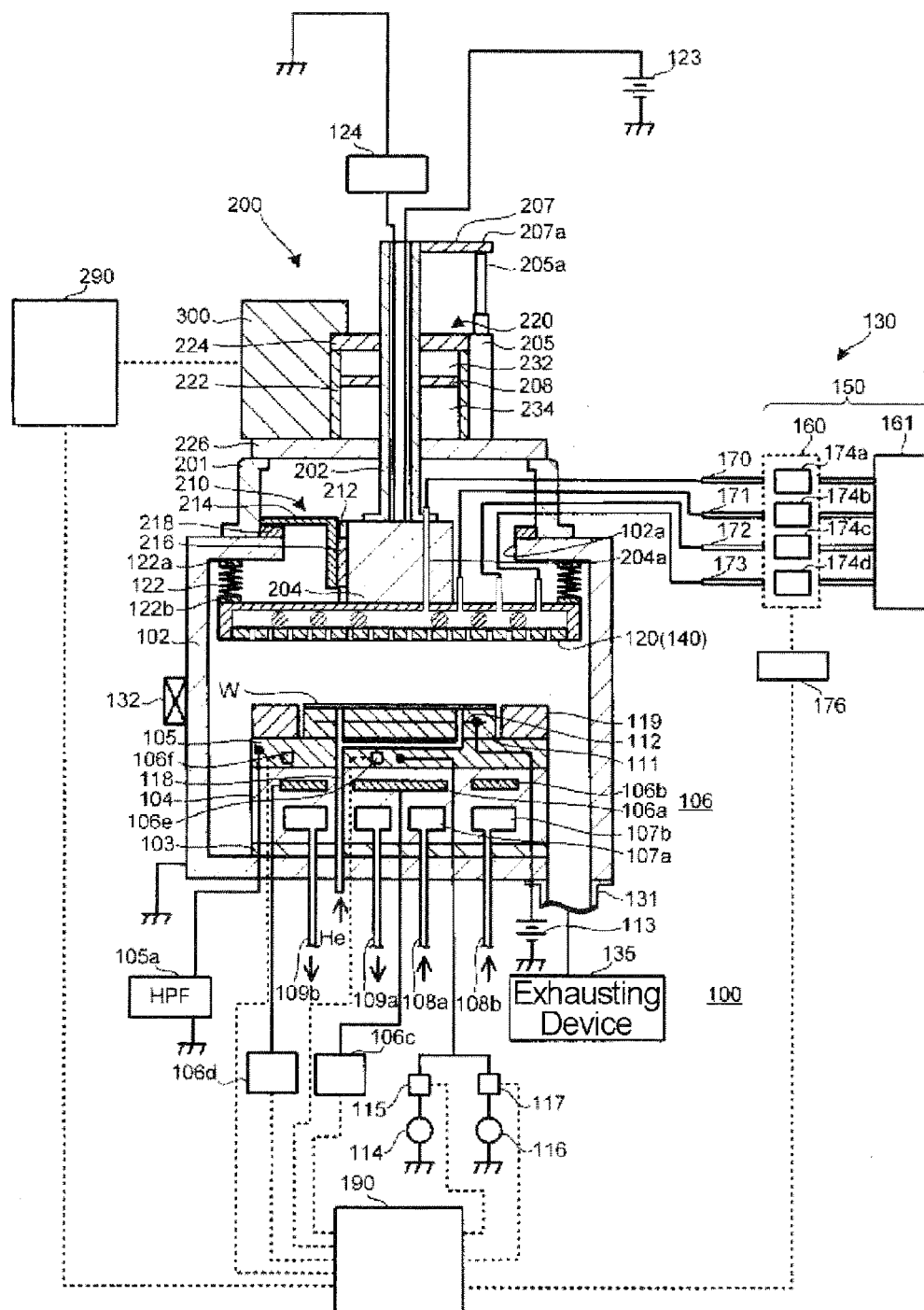


FIG.5A

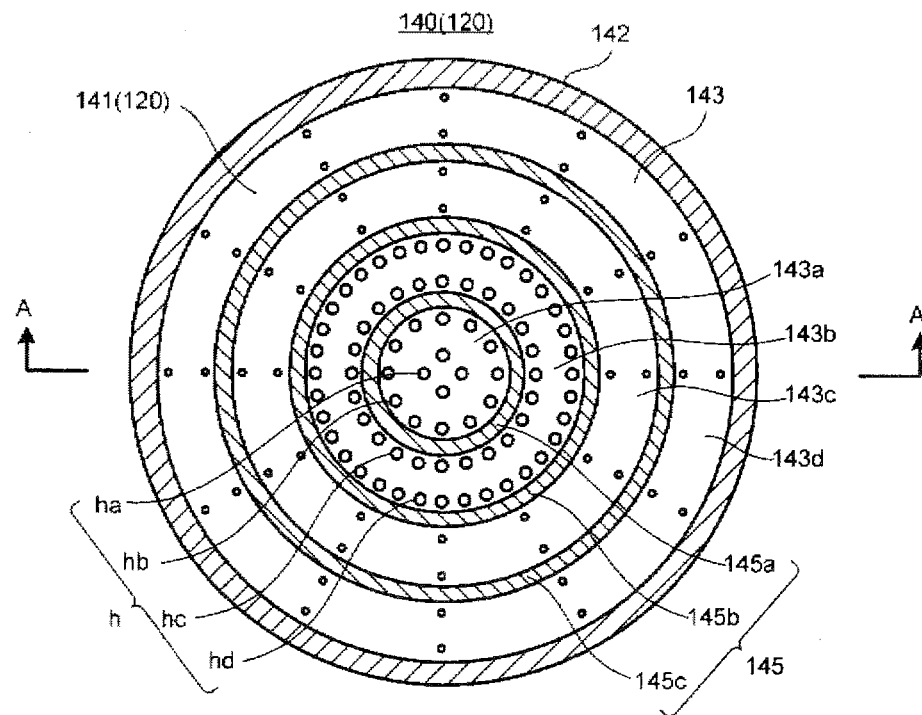


FIG.5B

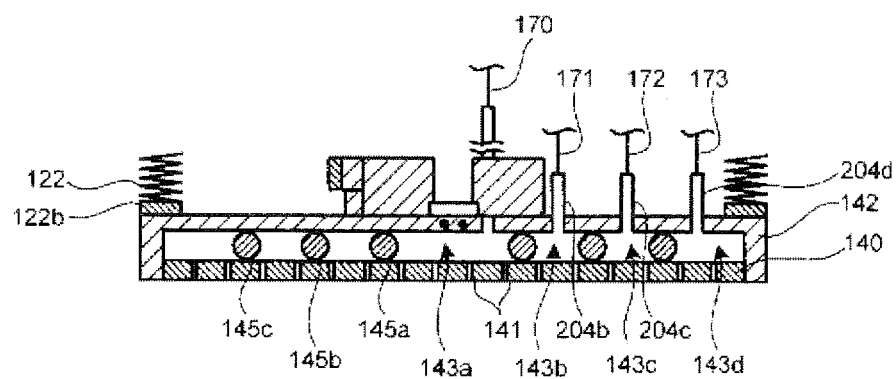


FIG. 6

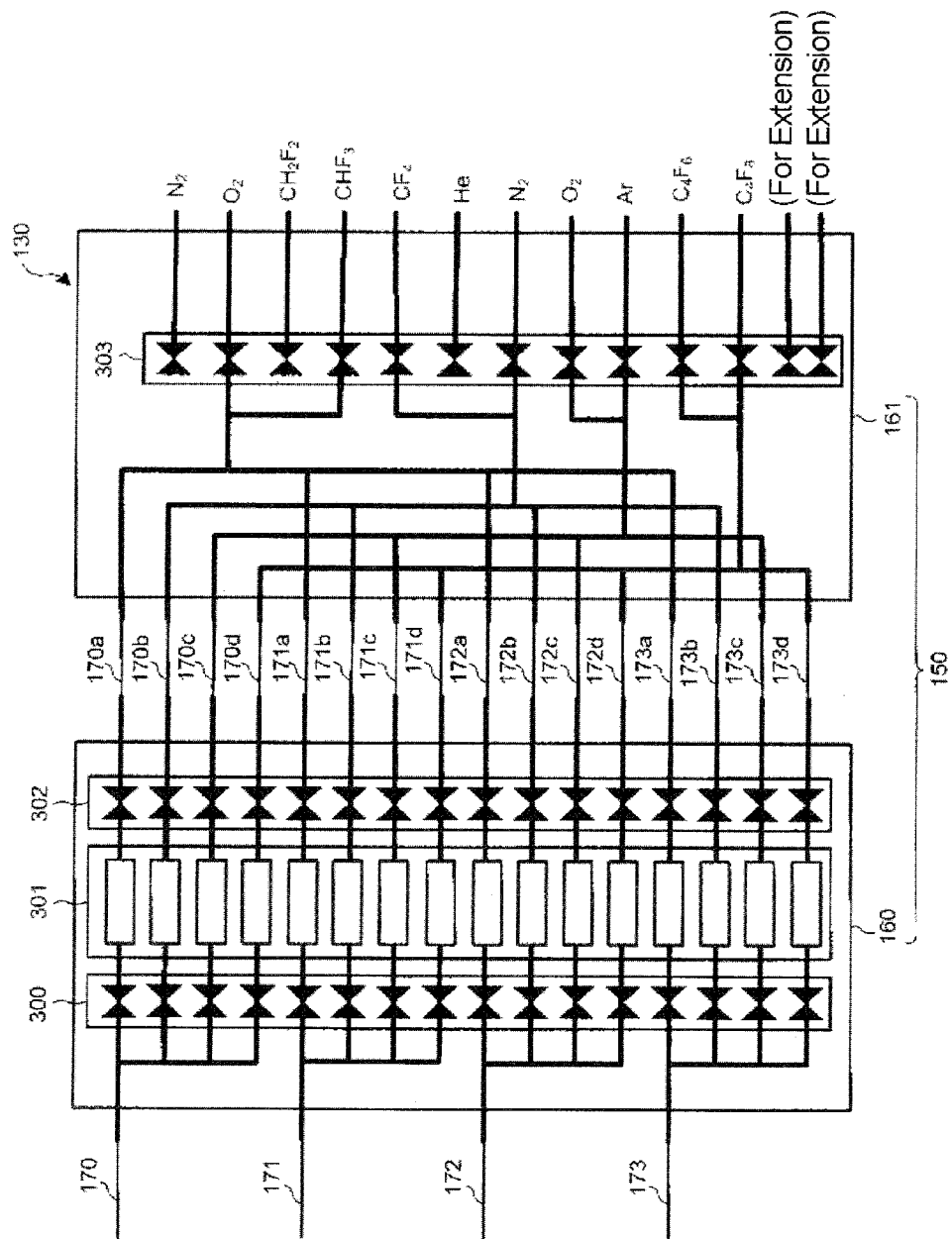


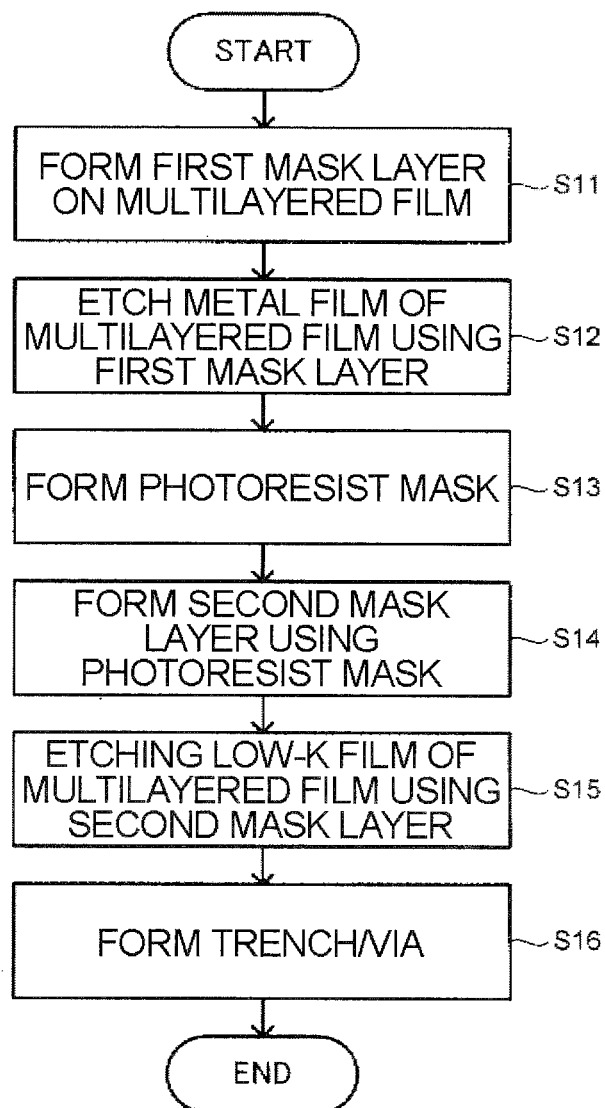
FIG. 7

FIG.8A

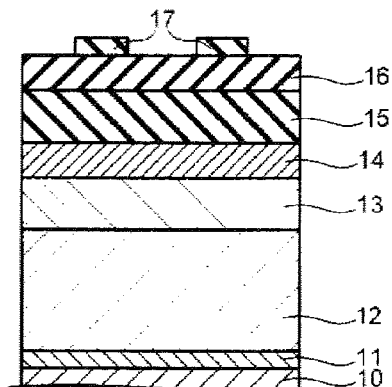


FIG.8D

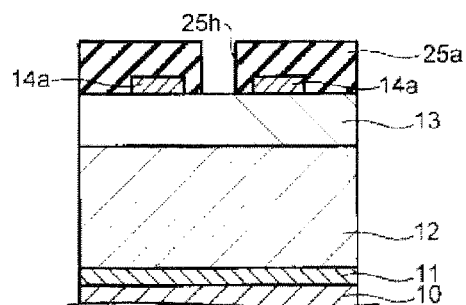


FIG.8B

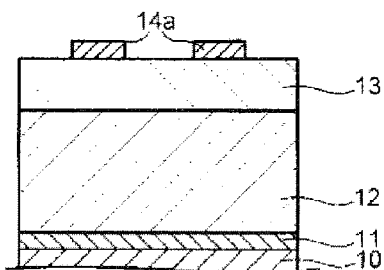


FIG.8E

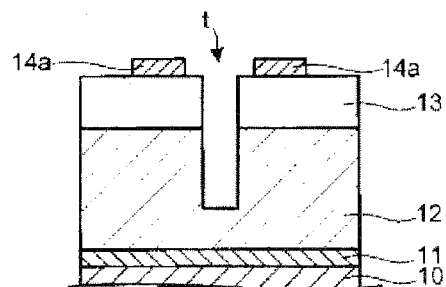


FIG.8C

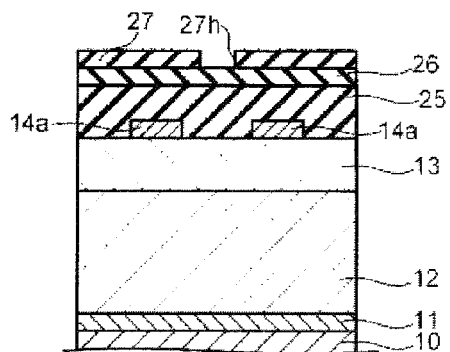


FIG.8F

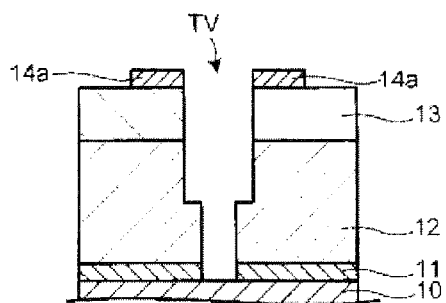
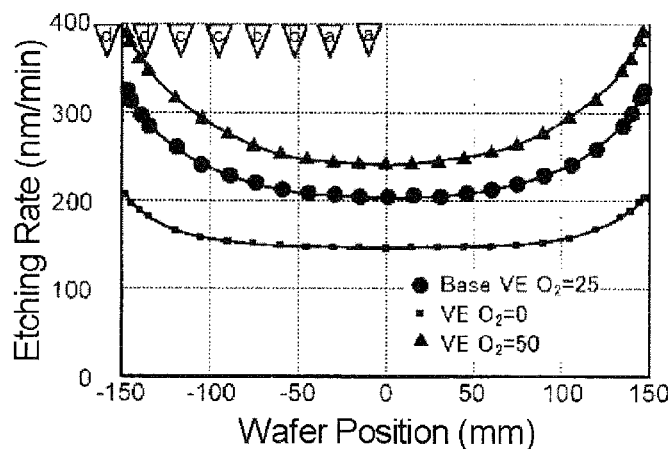
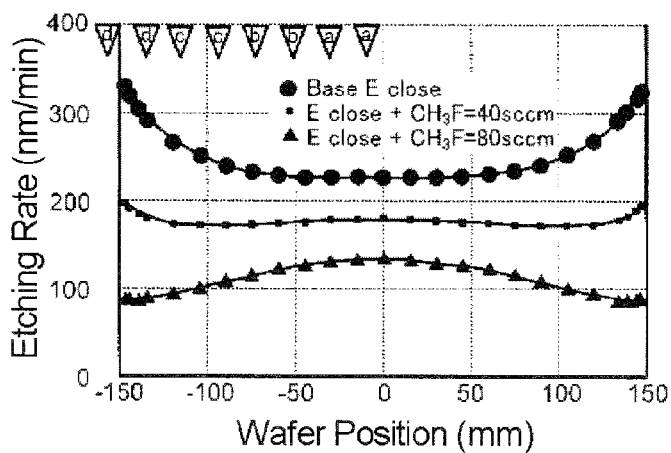
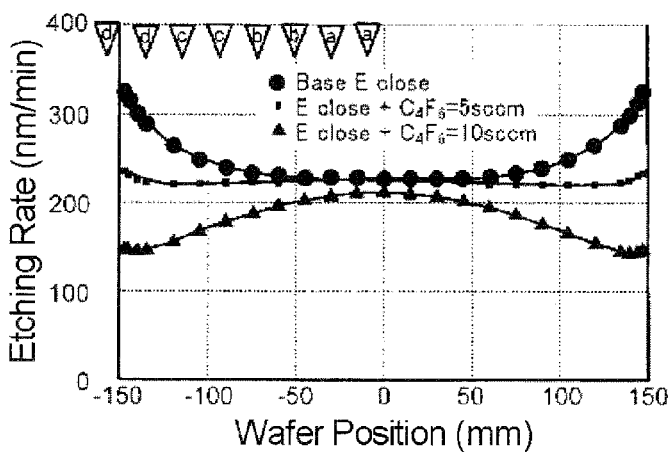


FIG. 9A**FIG. 9B****FIG. 9C**

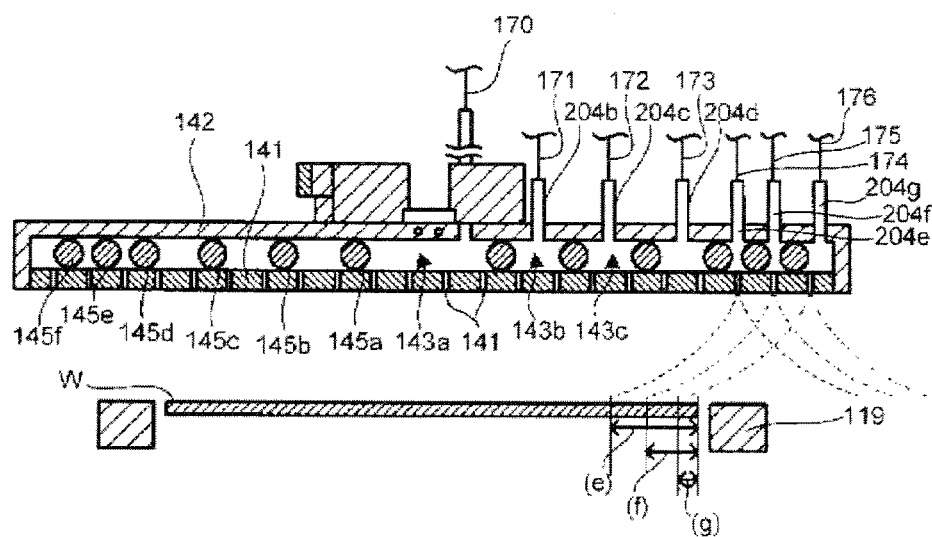


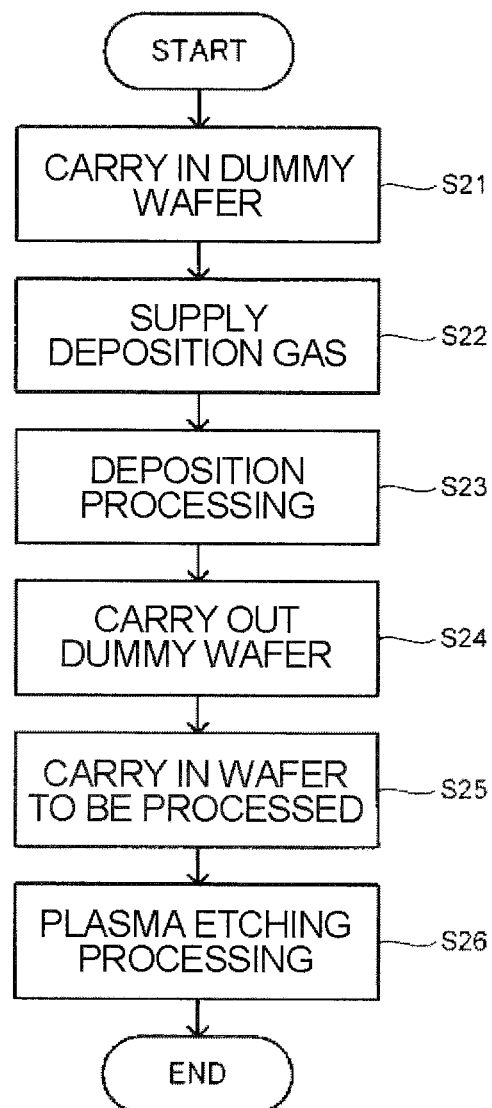
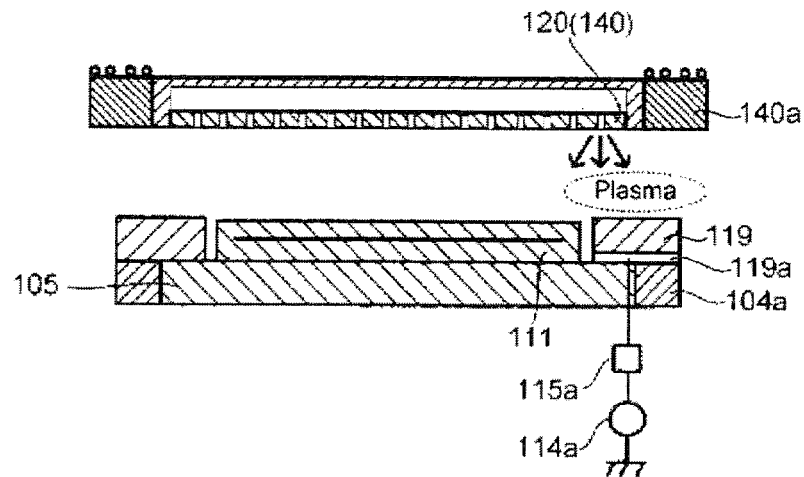
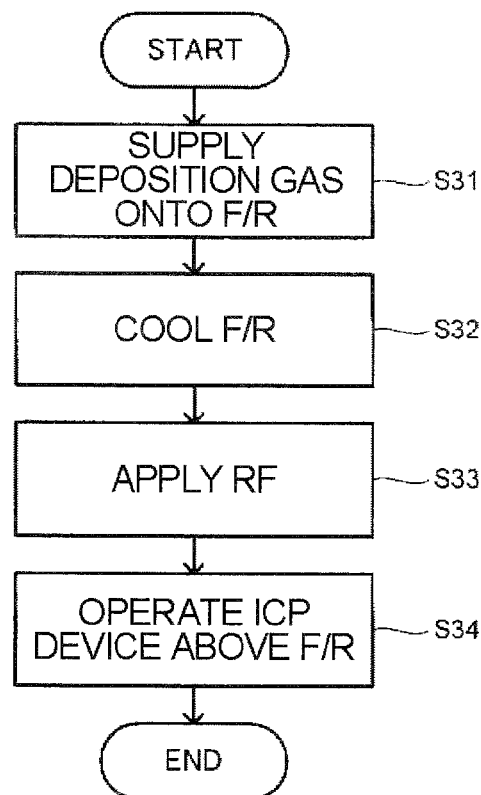
FIG.11

FIG.12A**FIG.12B**

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METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE

CROSS REFERENCE TO RELATED APPLICATION

This application is a 35 U.S.C. 371 National Phase Entry Application from PCT/JP2012/006850, filed Oct. 25, 2012, which claims the benefit of U.S. Provisional Application No. 61/557,458, filed Nov. 9, 2011 and Japanese Patent Application No. 2011-236694, filed Oct. 28, 2011, the disclosures of which are incorporated herein in their entirety by reference.

TECHNICAL FIELD

The present disclosure relates to a method of manufacturing a semiconductor device including a plasma etching process on a substrate.

BACKGROUND

As an apparatus for processing a substrate such as a semiconductor wafer (hereinafter, referred to as a "wafer") in a manufacturing process of a semiconductor device, there is a plasma etching device which etches a wafer by irradiating plasma onto the wafer.

In a plasma etching process, an etching gas including fluorine, chlorine, and oxygen is activated by a radio frequency electric field to generate plasma. The plasma includes active species such as charged particles (hereinafter, referred to as "ions") and neutral particles (hereinafter, referred to as "radicals"). The active species such as ions or radicals react with a wafer surface to generate a reaction product and the generated reaction product is volatilized so that the etching process is performed.

Recently, in the manufacturing process of a semiconductor device, since a diameter of a wafer is increased, it becomes difficult to uniformize an etching speed in a wafer plane. Therefore, in order to improve in-plane uniformity, it has been attempted to uniformize a density of the active species in a center area and a peripheral area in the wafer plane by adjusting the amount of an etching gas supplied from an upper electrode (See, e.g., Patent Document 1).

PRIOR ART DOCUMENT

Patent Document

Patent Document 1: Japanese Patent No. 4701776

SUMMARY OF DISCLOSURE

Technical Problems to be Solved

However, in the manufacturing process of a semiconductor device of the related art, when an under-layer organic resist film (e.g., amorphous carbon) is etched with plasma using an intermediate layer including an inorganic material and an upper layer photosensitive resist film which are formed thereon, as a mask, a mixture gas of O₂ gas and CH₄ gas is used as a processing gas. In this case, it is known that side etching easily occurs in a side wall so that a bowing phenomenon occurs. Specifically, there is a problem in that a difference in etched shape is caused at a central portion and a peripheral edge portion in a single semiconductor wafer.

The present disclosure has been made in an effort to provide a method of manufacturing a semiconductor device

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which may uniformize the etched shape at a central portion and a peripheral edge portion of a wafer.

Means to Solve the Problems

In order to solve the problems, an exemplary embodiment of the present disclosure provides a method of manufacturing a semiconductor device including a wafer using a plasma etching device which includes a chamber, a chuck provided in the chamber so as to dispose a wafer to be processed thereon, a focus ring disposed at a peripheral edge portion of the chuck to surround the disposed position of the wafer, and a gas supplying mechanism configured to supply various types of gases according to a position in a radial direction of the wafer. The method includes: placing a wafer formed with an organic film on the chuck; introducing an etching gas which etches the organic film on the wafer from the gas supplying mechanism to a central portion of the wafer; introducing an etching inhibiting factor gas having a property of reacting with the etching gas to the peripheral edge portion of the wafer from the gas supplying mechanism; and performing plasma etching on the wafer using the etching gas.

Advantageous Effect of Disclosure

A method of manufacturing a semiconductor device which may uniformize etched shape at a central portion and a peripheral edge portion of a wafer may be provided.

BRIEF DESCRIPTION OF DRAWINGS

FIG. 1A is a view illustrating a plasma etching state at a peripheral edge portion of a wafer.

FIG. 1B is a view illustrating a plasma etching state at a peripheral edge portion of a wafer.

FIG. 1C is a view illustrating in-plane uniformity of an etching rate in plasma etching.

FIG. 2A is a view illustrating a flow rate example of a processing gas in plasma etching of the related art.

FIG. 2B is a view illustrating an example in which a flow rate ratio at a central portion and a peripheral edge portion of a wafer is changed in the plasma etching illustrated in FIG. 2A.

FIG. 2C is a view illustrating in-plane uniformity of an etching rate in the plasma etching using the flow rate illustrated in FIGS. 2A and 2B.

FIG. 3A is a view illustrating an example in which a processing gas of the peripheral edge portion of the wafer is changed.

FIG. 3B is a view illustrating a function of a processing gas at the peripheral edge portion of the wafer.

FIG. 3C is a view illustrating a function of a processing gas at the peripheral edge portion of the wafer.

FIG. 4 is a view illustrating a configuration of a plasma etching device according to an exemplary embodiment.

FIG. 5A is a view illustrating a configuration of a shower head in the plasma etching device according to the exemplary embodiment.

FIG. 5B is a view illustrating the configuration of the shower head in the plasma etching device according to the exemplary embodiment.

FIG. 6 is a view illustrating a configuration of a gas supply device in the plasma etching device according to the exemplary embodiment.

FIG. 7 is a flowchart illustrating an example of a plasma etching method by the plasma etching device according to the exemplary embodiment.

FIG. 8A is a view illustrating a state in the vicinity of a surface of a wafer W when the plasma etching method illustrated in FIG. 7 is performed.

FIG. 8B is a view illustrating a state in the vicinity of the surface of the wafer W when the plasma etching method illustrated in FIG. 7 is performed.

FIG. 8C is a view illustrating a state in the vicinity of the surface of the wafer W when the plasma etching method illustrated in FIG. 7 is performed.

FIG. 8D is a view illustrating a state in the vicinity of the surface of the wafer W when the plasma etching method illustrated in FIG. 7 is performed.

FIG. 8E is a view illustrating a state in the vicinity of the surface of the wafer W when the plasma etching method illustrated in FIG. 7 is performed.

FIG. 8F is a view illustrating a state in the vicinity of the surface of the wafer W when the plasma etching method illustrated in FIG. 7 is performed.

FIG. 9A is a view illustrating in-plane uniformity of an etching rate when a flow rate of O_2 is changed at a central portion and a peripheral edge portion of a wafer in a plasma etching method according to an exemplary embodiment.

FIG. 9B is a view illustrating in-plane uniformity of an etching rate when CH_3F is supplied to a peripheral edge portion of the wafer as processing gas in a plasma etching method according to an exemplary embodiment.

FIG. 9C is a view illustrating in-plane uniformity of an etching rate when C_4F_6 is supplied to a peripheral edge portion of a wafer in a plasma etching method according to an exemplary embodiment.

FIG. 10A is a view illustrating a modified embodiment of a plasma etching device according to an exemplary embodiment.

FIG. 10B is a view illustrating a modified embodiment of a plasma etching device according to an exemplary embodiment.

FIG. 11 is a flowchart illustrating a modified embodiment of a semiconductor device manufacturing method according to an exemplary embodiment.

FIG. 12A is a view illustrating a modified embodiment of a plasma etching device according to an exemplary embodiment.

FIG. 12B is a flowchart illustrating an example of a method of manufacturing a semiconductor device by a plasma etching device illustrated in FIG. 12A.

DETAILED DESCRIPTION TO EXECUTE THE INVENTION

(Wafer In-Plane Deviation of E/R)

In plasma etching which etches an organic film, it is known that an etching rate is higher at a peripheral edge portion of a wafer than at a central portion thereof. This is considered because O radical on a focus ring contributes to etching of the peripheral edge portion of the wafer and a difference of materials of the wafer and the focus ring contributes to the difference in etching rate. Ununiformity of an etching rate in a wafer plane may cause a bowing or an undercut phenomenon which occurs at a side wall of an organic film which exist in a lowest layer of a multilayered resist mask.

FIGS. 1A and 1B illustrate a plasma etching state at a peripheral edge portion of a wafer. As illustrated in FIG. 1A, it is assumed that a wafer W disposed on an electrostatic chuck 111 is subjected to plasma etching. A focus ring 119 is formed of a dielectric material such as ceramics or quartz or a conductive material such as monocrystalline silicon. However, when an organic film is formed on the wafer W, a

reaction mechanism may vary on the organic film and the focus ring. For example, even when, on the organic film of the wafer W, O radicals react with the organic film to be turned into CO and separated, the O radicals on the focus ring 119 are not consumed by the reaction. Therefore, the O radicals on the focus ring 119 are surplus to contribute to etching of the peripheral edge portion of the wafer W. That is, the etching rate at the peripheral edge portion of the wafer is increased.

Here, as illustrated in FIG. 1B, a change of the etching rate when a polyimide sheet film is adhered on the focus ring 119 to have reactivity with the O radicals was researched. FIG. 1C illustrates comparison results of etching rates in the case when the polyimide sheet film was adhered on the focus ring 119 and in the case when the polyimide sheet film was not adhered thereon (Base). As illustrated in FIG. 1C, when the focus ring was exposed, the etching rate at the peripheral edge portion of the wafer was suddenly increased. Meanwhile, when the polyimide sheet film was adhered on the focus ring 119 to have reactivity with the O radicals, the etching rate was substantially uniform from the center to the peripheral edge portion of the wafer. Therefore, it can be appreciated that when surplus O radicals are suppressed on the focus ring, an in-plane etching rate of a wafer plane formed with an organic film may be uniformized.

(Improvement of E/R at Wafer Edge Area)

In the organic film etching, a shape control may be enabled when oxygen gas or rare gas is added to a processing gas. Further, it is known that, when a concentration of an inert gas is increased, an etching state at the side wall is desirable. Therefore, a method of suppressing a flow rate of O_2 gas at the peripheral edge portion of the wafer and increasing a flow rate of O_2 gas at the central portion of the wafer is considered.

FIG. 2A illustrates an example of a flow rate of a processing gas in plasma etching of the related art and FIG. 2B illustrates an example in which a flow rate of the processing gas varies at the central portion and the peripheral edge portion of the wafer in the plasma etching illustrated in FIG. 2A. As compared with the flow rate of the processing gas of the related art illustrated in FIG. 2A, in the example illustrated in FIG. 2B, the O_2 gas flow rate is increased at the central portion (Center), a middle area (Middle), and an edge portion (Edge) of the wafer and the O_2 gas flow rate is set to be zero at the peripheral edge portion (Very Edge) of the wafer.

FIG. 2C illustrates wafer in-plane etching rates of the plasma etching according to conditions of FIGS. 2A and 2B. As illustrated in FIG. 2C, it can be appreciated that the sudden increase of the etching rate in the vicinity of the peripheral edge portion of the wafer is not still completely resolved only by controlling the O_2 gas flow rate. As described above, it can be appreciated that there is a limitation in controlling an amount of the O radicals generated at the peripheral edge portion of the wafer and outside of the peripheral edge portion only by controlling a wafer in-plane distribution of a supplied amount of a processing gas.

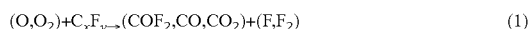
(Use of Scavenger Effect)

In the plasma etching according to the exemplary embodiment, a processing gas having an effect (scavenger effect) of removing surplus O radicals at the peripheral edge portion of the wafer is supplied to the peripheral edge portion of the wafer. That is, a gas such as, for example, CH_3F or C_4F_6 is introduced to the peripheral edge portion of the wafer. For example, as illustrated in FIG. 3A, C_4F_6 gas is supplied to the wafer at the peripheral edge portion of the wafer, instead of O_2 gas.

As illustrated in FIGS. 3B and 3C, a gas having the scavenger effect (etching inhibiting factor gas) reacts with the surplus O radicals on the focus ring 119. For example, as

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illustrated in FIG. 3B, when C_xF_y gas is introduced to the peripheral edge portion of the wafer W, an unsaturated species selectively reacts with the O radicals. Thus, a reaction as indicated in Equation (1) is exhibited.



That is, the surplus O radicals may be removed.

As described above, in the plasma etching according to the exemplary embodiment, the etching inhibiting factor gas is introduced to the peripheral edge portion of the wafer to remove the surplus O radicals. Therefore, in a plasma etching device which implements the plasma etching according to the exemplary embodiment (and a manufacturing device which implements a method of manufacturing a semiconductor device including the plasma etching), it is required not only to control a flow rate of an introduced gas in a radial direction of the wafer but also to select and control a gas species introduced in the radial direction of the wafer. (Configuration of Manufacturing Device according to Exemplary Embodiment)

An example of a plasma etching device which is suitable for a semiconductor device manufacturing method according to an exemplary embodiment will be described with reference to FIG. 4.

As illustrated in FIG. 4, a plasma etching device 100 includes a chamber (processing container) 102 formed in a cylindrical shape having a surface which is formed of, for example, treated by aluminum anodic oxidation (alumite process). The chamber 102 is grounded. A susceptor support 104 having a substantially cylindrical shape is installed on the bottom of the chamber 102 through an insulating plate 103 such as a ceramic. A susceptor 105 which configures a lower electrode is installed on the susceptor support 104. The susceptor 105 is grounded via a high pass filter (HPF) 105a.

The susceptor 105 is formed in a disk shape whose top side central portion is concave. The electrostatic chuck 111 having a diameter which is substantially the same as the diameter of the wafer W which is an example of an object to be processed is provided on the susceptor 105. The electrostatic chuck 111 includes insulating materials which are formed of disk-shaped ceramic members and an electrostatic electrode 112 interposed between the insulating materials. Further, a DC power source 113 is connected to the electrostatic electrode 112 of the electrostatic chuck 111. For example, when a DC voltage of 1.5 kV is applied to the electrostatic electrode 112 from the DC power source 113, the wafer W is attracted to and held on the electrostatic chuck 111.

A first radio frequency power source 114 is connected to the susceptor 105 through a first matching unit 115 and a second radio frequency power source 116 is connected to the susceptor 105 through a second matching unit 117. The first radio frequency power source 114 applies a bias power having a first frequency, for example, a frequency of 13.6 MHz, to the susceptor 105. The second radio frequency power source 116 applies a plasma generating power having a second frequency, for example, a frequency of 40 MHz, to the susceptor 105. Plasma is generated in the chamber 102 by the plasma generating power.

A gas passage 118 is formed in the insulating plate 103, the susceptor support 104, the susceptor 105, and the electrostatic chuck 111 so as to supply a heat transferring medium (e.g., a backside gas such as He gas) onto a rear surface of the wafer W. Heat transfer is performed between the susceptor 105 and the wafer W through the heat transferring medium and the wafer W is maintained at a predetermined temperature.

A ring shaped focus ring 119 (F/R) is disposed at an peripheral edge portion of the top side of the susceptor 105 so as to

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surround the wafer W supported on the electrostatic chuck 111. The focus ring 119 is formed of a dielectric material such as ceramics or quartz or a conductor, for example, a conductive material such as the monocrystalline silicon which is the same as the material which configures the wafer W.

When a distribution region of the plasma extends to the top of the focus ring 119, the density of the plasma outside of the peripheral edge portion of the wafer W may be maintained at a level that is substantially equal to a density of the plasma at the central portion of the wafer W. Therefore, the uniformity of the plasma etching in the plane of the wafer W may be improved.

An upper electrode 120 is provided above the susceptor 105 to face the susceptor 105 in parallel. The upper electrode 120 also functions as a shower head 140 (described below) which supplies an etching gas toward the wafer W supported by the susceptor 105. The DC power source 123 is connected to the upper electrode 120. Further, the upper electrode 120 is grounded via a low pass filter (LPF) 124.

The upper electrode 120 is configured to be driven in a vertical direction by an upper electrode driving unit 200. The upper electrode 120 is configured to be driven in the vertical direction so that a distance (hereinafter, referred to as a "gap") G of a space between the upper electrode 120 and the susceptor 105 may be adjusted. Since the gap G is a parameter which significantly affects the diffusion and flow of the etching gas, the plasma distribution between the upper electrode 120 and the susceptor 105 in the chamber 102 may be controlled when the gap G is configured to be adjustable.

A movement amount of the upper electrode 120, which is driven by the upper electrode driving unit 200, in the vertical direction is not particularly limited. For example, it is possible to adopt a structure in which the movement amount of the upper electrode 120 in the vertical direction is 70 mm and the gap G is adjusted to be equal to or larger than 20 mm and equal to or smaller than 90 mm. Further, the plasma etching device 100 may have a configuration obtained by rotating the configuration illustrated in FIG. 4 by 90° and horizontally tilting the configuration, or a configuration obtained by turning the configuration upside down.

The upper electrode 120 may be supported on a top inner wall of the chamber 102 by a bellows 122. The bellows 122 is attached to the top inner wall of the chamber 102 through an annular upper flange 122a by fixing means such as bolts and attached to the top surface of the upper electrode 120 through an annular lower flange 122b by the fixing means such as bolts.

A configuration of the upper electrode driving unit 200 which may adjust the gap G will be described in detail. The upper electrode driving unit 200 includes a substantially cylindrical support member 204 which supports the upper electrode 120. The support member 204 is attached at a substantially center of the top of the upper electrode 120 by, for example, bolts. The support member 204 is disposed to be capable of going in and out of a hole 102a which is formed at a substantially center of the top wall of the chamber 102. Specifically, an outer peripheral surface of the support member 204 is supported inside the hole 102a of the chamber 102 through a sliding mechanism 210. The sliding mechanism 210 includes a guide member 216 which is fixed through the fixing member 214 having a L-shaped cross-section to the vertical portion of the fixing member 214, for example, in the upper portion of the chamber, and a rail unit 212 which is slidably supported by the guide member 216 and formed in one direction (a vertical direction in this exemplary embodiment) on the outer peripheral surface of the support member 204.

The horizontal portion of the fixing member **214** which fixes the guide member **216** of the sliding mechanism **210** is fixed to the upper portion of the chamber **102** through an annular horizontal adjusting plate **218**. The horizontal position of the upper electrode **120** is adjusted by the horizontal adjusting plate **218**. The horizontal adjusting plate **218** is fixed to the chamber **102** by a plurality of bolts which are disposed in a circumferential direction of the horizontal adjusting plate **218** at regular intervals. Further, the inclination amount of the horizontal adjusting plate **218** with respect to the horizontal direction may be adjusted by the protruding amount of the bolts. The inclination with respect to the horizontal direction is adjusted by the horizontal adjusting plate **218** and the inclination with respect to the vertical direction is adjusted by the guide member **216** of the sliding mechanism **210** so that the inclination of the upper electrode **120** in the horizontal direction may be adjusted. That is, the upper electrode **120** may be always maintained in the horizontal position.

At the top side of the chamber **102**, a pneumatic cylinder **220** is attached to the chamber **102** through a cylindrical body **201** in which the pneumatic cylinder **220** is configured to drive the upper electrode **120**. That is, the lower end of the cylindrical body **201** is air-tightly attached by bolts to cover the hole **102a** of the chamber **102** and the upper end of the cylindrical body **201** is air-tightly attached to the lower end of the pneumatic cylinder **220**.

The pneumatic cylinder **220** has a rod **202** which may be driven in one direction. The lower end of the rod **202** is connected to a substantially center of the top surface of the support member **204** by, for example, bolts. When the rod **202** is driven, the upper electrode **120** may be moved by the support member **204** along the sliding mechanism **210**. The rod **202** is configured in a cylindrical shape and an inner space of the rod **202** communicates with a central hole which is formed at a substantially center of the support member **204** and opened to the atmosphere. Accordingly, a wiring grounded via the upper electrode **120** and the low pass filter (LPF) **124** and a feeder line configured to apply a DC voltage from the DC power source **123** to the upper electrode **120** may be wired to be connected to the upper electrode **120** through the central hole of the support member **204** from the inner space of the rod **202**.

A position detecting unit configured to detect the position of the upper electrode **120** such as, for example, a linear encoder **205**, is provided on a side portion of the pneumatic cylinder **220**. In the meantime, an upper end member **207** having an extending portion **207a** which extends laterally from the rod **202** is provided at the upper end of the rod **202**. The extending portion **207a** of the upper end member **207** and a detecting unit **205a** of the linear encoder **205** are abutted to each other. The upper end member **207** moves in response to the movement of the upper electrode **120** so that the position of the upper electrode **120** may be detected by the linear encoder **205**.

The pneumatic cylinder **220** includes a cylindrical cylinder body **222**, an upper support plate **224**, and a lower support plate **226**. The cylindrical cylinder body **222** is configured to be sandwiched between the upper support plate **224** and the lower support plate **226**. An annular partitioning member **208** configured to partition the pneumatic cylinder **220** into an upper space **232** and a lower space **234** is provided on the outer peripheral surface of the rod **202**.

The upper space **232** of the pneumatic cylinder **220** is configured such that compressed air is introduced from an upper port (not illustrated) of the upper support plate **224** into the upper space **232** of the pneumatic cylinder **220**. Further,

the lower space **234** of the pneumatic cylinder **220** is configured such that compressed air is introduced from a lower port (not illustrated) of the lower support plate **226** into the lower space **234** of the pneumatic cylinder **220**. When the amount of air introduced from the upper port and the lower port into the upper space **232** and the lower space **234** is controlled, the rod may be controlled to be driven in one direction (for example, in the vertical direction). The amount of air introduced into the pneumatic cylinder **220** is controlled by a pneumatic circuit **300** which is provided in the vicinity of the pneumatic cylinder **220**.

The upper electrode driving unit **200** includes a controller **290** which is connected to a device controller **190**. A control signal from the device controller **190** is transmitted to the controller **290** and each component of the upper electrode driving unit **200** is controlled to be driven by the controller **290**.

A temperature distribution adjusting unit **106** is disposed inside the susceptor support **104** in which the temperature distribution adjusting unit **106** is configured to adjust the in-plane temperature distribution of the wafer W. The temperature distribution adjusting unit **106** includes heaters **106a** and **106b**, power sources **106c** and **106d** for heaters, thermometers **106e** and **106f**, and refrigerant flow channels **107a** and **107b**.

A center side heater **106a** and an outer periphery side heater **106b** are disposed inside the susceptor support **104** from the center toward the outer periphery side. The power source **106c** for the center side heater is connected to the center side heater **106a** and the power source **106d** for the outer periphery side heater is connected to the outer periphery side heater **106b**. The power source **106c** for the center side heater and the power source **106d** for the outer periphery side heater may independently adjust the power supplied to the center side heater **106a** and the power supplied to the outer periphery side heater **106b**, respectively. Therefore, the temperature distribution along the radial direction of the wafer W may be formed on the susceptor support **104** and the susceptor **105**. That is, the temperature distribution along the radial direction of the wafer W may be adjusted.

A center side thermometer **106e** and an outer periphery side thermometer **106f** are disposed inside the susceptor support **104** from the center side to the outer periphery side. The center side thermometer **106e** and the outer periphery side thermometer **106f** measure the temperatures of the central portion and the outer peripheral edge portion of the susceptor support **104**, respectively, so that the temperatures of the center side and the outer periphery side of the wafer W can be derived. The temperatures measured by the center side thermometer **106e** and the outer periphery side thermometer **106f** are transmitted to the device controller **190**. The device controller **190** adjusts outputs of the power source **106c** for the center side heater and the power source **106d** for the outer periphery side heater so that the temperatures of the wafer W derived from the measured temperatures become a target temperatures.

A center side refrigerant flow channel **107a** and an outer periphery side refrigerant flow channel **107b** may be provided inside the susceptor support **104** from the center side toward the outer periphery side. In addition, for example, cooling waters or fluorocarbon based refrigerants of different temperatures may be circulated in the flow channels **107a**, **107b**, respectively. When the refrigerant is circulated, the refrigerant is introduced into the center side refrigerant flow channel **107a** through a center side introduction pipe **108a** and discharged from a center side discharging pipe **109a**. In the meantime, the refrigerant is introduced into the outer periph-

ery side refrigerant flow channel **107b** through an outer periphery side introduction pipe **108b** and discharged from an outer periphery side discharging pipe **109b**.

The temperature of the susceptor **105** is adjusted by heating by the heaters **106a** and **106b** and cooling from the refrigerant. Therefore, the wafer **W** is adjusted to have a predetermined temperature determined by a heated part by radiation from the plasma or irradiation of ions included in the plasma and the exchange of calories with the susceptor **105**. Further, the susceptor support **104** includes the center side heater **106a** (and the center side refrigerant flow channel **107a**) and the outer periphery side heater **106b** (and the outer periphery side refrigerant flow channel **107b**). Therefore, the temperatures of the wafer **W** may be independently adjusted at the center side and the outer periphery side.

An insulator or a space may be provided between the center side heater **106a** and the outer periphery side heater **106b** or between the center side refrigerant flow channel **107a** and the outer periphery side refrigerant flow channel **107b** as an insulating layer. When the insulating layer is provided, the center side heater **106a** and the outer periphery side heater **106b**, or the center side refrigerant flow channel **107a** and the outer periphery side refrigerant flow channel **107b** may be thermally blocked from each other. That is, a larger temperature distribution may occur between the center side and the outer periphery side of the wafer **W**.

An exhaust pipe **131** is connected to the bottom of the chamber **102** and an exhausting device **135** is connected to the exhaust pipe **131**. The exhausting device **135** includes a vacuum pump such as a turbo molecular pump and adjusts the inside of the chamber **102** to a predetermined decompressed atmosphere (for example, 0.67 Pa or lower). Further, a gate valve **132** is provided on the side wall of the chamber **102**. When the gate valve **132** is opened, a wafer **W** may be carried into the chamber **102** or carried out of the chamber **102**. A conveying arm is used for conveying the wafer **W**.

Subsequently, the shower head **140** will be described with reference to FIGS. **5A** and **5B**. As illustrated in FIG. **5A**, the shower head **140** includes a circular electrode plate **141** (upper electrode **120**) having a plurality of gas jetting holes **h** (ha to hd) so as to supply gas such as an etching gas to the wafer **W**, and an electrode support **142** configured to detachably support the top surface side of the electrode plate **141**. The electrode support **142** has a disk shape having an outer diameter which is the same as the outer diameter of the electrode plate **141** and a circular buffer chamber **143** is formed inside the electrode support **142**.

In the buffer chamber **143**, one or more annular partitioning members **145** which are formed of, for examples, O rings are disposed on the electrode plate **141**, as illustrated in FIG. **5A**. Specifically, according to the present exemplary embodiment, three ring shaped partitioning members **145a**, **145b**, and **145c** having different diameters are concentrically disposed. Therefore, the buffer chamber **143** is divided into a central area **143a** (Center), a middle area **143b** (Middle), a peripheral edge area **143c** (Edge), and an outermost peripheral edge area **143d** (Very Edge) along the radial direction of the electrode plate **141**.

As illustrated in FIGS. **4** and **5B**, the areas **143a** to **143d** are connected to a gas supplying device **150** such that the etching gas is supplied to the areas **143a** to **143d** from the gas supplying device **150**. The etching gas supplied to the areas **143a** to **143d** is jetted toward the wafer **W** supported by the susceptor **105** from the corresponding gas jetting holes **h**.

The number and arrangement of gas jetting holes **h** may be determined such that the etching gas may be uniformly jet onto the wafer **W**. For example, the gas jetting holes **h** may be

disposed on circumferences of a plurality of concentric circles which is concentrically disposed with respect to the center of the shower head **140** (the electrode plate **141**). Specifically, when a wafer **W** having a diameter of 300 mm is used, in the central area **143a**, four (4) gas jetting holes **ha** are disposed (e.g., at regular intervals) on the circumference of a circle having a radius of 11 mm and twelve (12) gas jetting holes **hb** are disposed (e.g., at regular intervals) on the circumference of a circle having a radius of 33 mm. In the middle area (**143b**), twenty four (24) gas jetting holes **hc** are disposed (e.g., at regular intervals) on a circumference of a circle having a radius of 55 mm and thirty six (36) gas jetting holes **hd** are disposed (e.g., at regular intervals) on a circumference of a circle having a radius of 77 mm. Although not illustrated, in the peripheral edge area **143c**, forty eight (48) gas jetting holes are disposed (e.g., at regular intervals) on a circumference of a circle having a radius of 99 mm and sixty (60) gas jetting holes are disposed (e.g., at regular intervals) on a circumference of a circle having a radius of 121 mm. Although not illustrated, in the outermost peripheral edge area **143d**, eighty (80) gas jetting holes are disposed (e.g., at regular intervals) on a circumference of a circle having a radius of 143 mm and one hundred (100) gas jetting holes are disposed (e.g., at regular intervals) on a circumference of a circle having a radius of 165 mm.

Next, the gas supplying device **150** and a gas supplying system configured to separately supply the etching gas to each of the areas **143a** to **143d** of the buffer chamber **143** will be described with reference to FIG. **6**. The gas supplying device **150** includes a first gas box **161** and a second gas box **160**. The first gas box **161** accommodates a first collecting valve **303** which is connected to a plurality of gas supplying sources (not illustrated) and the second gas box **160** accommodates a second collecting valve **302**, flow controllers **301** such as mass flow controllers which are provided to correspond to the valves of the second collecting valve **302**, respectively, and a third collecting valve **300**.

In the present exemplary embodiment, a gas such as CF_4 , C_4F_6 , C_4F_8 , CH_2F_2 , or CHF_3 as a fluorocarbon based fluorine compound (CF based) is sealed in the gas supplying source. Similarly, oxygen (O_2) gas is sealed as a gas which controls the attachment of a CF based reaction product. Further, a rare gas such as Ar or He or N_2 gas is sealed as a carrier gas.

A pipe from each gas supplying source is connected to a corresponding valve in the first collecting valve **303** in the first gas box **161**. Further, in the present exemplary embodiment, a CHF_3 gas pipe and an O_2 gas pipe are joined to each other and branched into four branch pipes **170a**, **171a**, **172a**, and **173a** at the downstream side of the first collecting valve **303**. The first collecting valve **303** is controlled in such a manner that any of CHF_3 gas and O_2 gas flows in the branch pipes **170a** to **173a**.

Similarly, a CF_4 gas pipe and a N_2 gas pipe are joined to each other and branched into four branch pipes **170b**, **171b**, **172b**, and **173b** at the downstream side of the first collecting valve **303**. The first collecting valve **303** is controlled in such a manner that any of CF_4 gas and N_2 gas flows in the branch pipes **170b** to **173b**.

Similarly, an O_2 gas pipe and an Ar gas pipe are joined to each other and branched into four branch pipes **170c**, **171c**, **172c**, and **173c** at the downstream side of the first collecting valve **303**. The first collecting valve **303** is controlled in such a manner that any of O_2 gas and Ar gas flows in the branch pipes **170c** to **173c**.

A C_4F_6 gas pipe and a C_4F_8 gas pipe are joined to each other and branched into four branch pipes **170d**, **171d**, **172d**, and **173d** at the downstream side of the first collecting valve **303**.

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The first collecting valve **303** is controlled in such a manner that any of C_4F_6 gas and C_4F_8 gas flows in the branch pipes **170d** to **173d**.

The branch pipes **170a** to **173a**, **170b** to **173b**, **170c** to **173c**, and **170d** to **173d** are connected to corresponding valves in the second collecting valve **302** in the second gas box **160**, respectively, and also connected to the corresponding valves of the third collecting valve **300** through the corresponding flow controllers **301**, respectively.

Pipes corresponding to the branch pipes **170a**, **170b**, **170c**, and **170d** are joined to the pipe **170** at the downstream side of the third collecting valve **300** and the pipe **170** communicates with the central area **143a** of the shower head **140** (see FIG. 5B). Further, pipes corresponding to the branch pipes **171a**, **171b**, **171c**, and **171d** are joined to the pipe **171** at the downstream side of the third collecting valve **300** and the pipe **171** communicates with the middle area **143b** of the shower head **140** (see FIG. 5B). Similarly, pipes corresponding to the branch pipes **172a**, **172b**, **172c**, and **172d** are joined to the pipe **172** at the downstream side of the third collecting valve **300** and the pipe **172** communicates with the peripheral edge area **143c** of the shower head **140** (see FIG. 5B). Further, pipes corresponding to the branch pipes **173a**, **173b**, **173c**, and **173d** are joined to the pipe **173** at the downstream side of the third collecting valve **300** and the pipe **173** communicates with the outermost peripheral edge area **143d** of the shower head **140** (see FIG. 5B).

With the above configuration, the third collecting valve **300**, the second collecting valve **302**, and the first collecting valve **303** are appropriately opened or closed so that each etching gas may be selectively supplied to each the areas **143a** to **143d** of the shower head **140**. That is, in the example of FIG. 6, each of the pipes connected to the gas supplying sources is branched into four pipes, like the pipes **170** to **173**. Further, the pipes are connected to the first collecting valve **303** and configured to be capable of switching the gas species in accordance with a desired process. With this configuration, addition of a new gas supplying source or stopping of supplying an etching gas which is not required by a process may be conducted through simple manipulation.

As described above, the plasma etching device **100** includes the device controller **190**. The device controller **190** includes an arithmetic processing device (not illustrated) which includes a CPU and a recording medium (not illustrated) which includes a hard disk. The device controller **190** controls an operation of each component of the first radio frequency power source **114**, the second radio frequency power source **116**, the temperature distribution adjusting unit **106**, the upper electrode driving unit **200** and a gas supplying condition adjusting unit **130** which have been described above. When operating each component, the CPU of the device controller **190** controls the component according to a program recorded in the hard disk of the device controller **190** and corresponding to each etching processing.

(Operation of Manufacturing Device according to Exemplary Embodiment)

Next, operations of a manufacturing device according to an exemplary embodiment which is performed using a plasma etching device **100** will be described with reference to FIGS. 4 to 8D. FIG. 7 is a flowchart illustrating a process of a semiconductor device manufacturing method according to an exemplary embodiment, and FIGS. 8A to 8D are views illustrating states of a wafer W in respective processes. For the convenience, FIGS. 8A to 8D illustrate one of a plurality of trench/via structures which are formed on a wafer. Further, the processes illustrated in FIGS. 8A to 8D are continuously performed in the plasma etching device **100**.

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First, as illustrated in FIG. 8A, a block layer **11**, a low dielectric (low-k) layer **12**, a silicon oxide film **13**, a titanium nitride (TiN) layer **14**, an organic planarization layer **15**, an anti-reflection film **16**, and a first mask layer **17** are formed on a wiring layer **10** formed on a wafer in this order as a multi-layered film (step S11 of FIG. 7, hereinafter, referred to as "S11").

The block layer **11** is formed of a material such as, for example, silicon oxide, using a plasma CVD method. The block layer **11** is formed between the wiring layer **10** and the low-k film **12** to reduce the degradation of the wiring layer **10** caused by the low-k film **12** so as to protect the wiring layer **10**.

The low-k film **12** is formed by a low dielectric material having a low dielectric constant of about 3.5 or less. The low-k film **12** may be formed of, for example, Black Diamond (registered trade mark), silicon oxide to which an impurity such as SiOF or SiOC is added, or a porous material. Further, the low-k film **12** may be formed of a spin-on material having hydrogen silsesquioxane (HSQ) or methylsilsesquioxane (MSQ) as a main component. In the present exemplary embodiment, the low-k film **12** is formed of Black Diamond.

The silicon oxide film **13** may be formed by an oxygen plasma CVD method using tetraethoxysilane (TEOS) as a raw material. The organic planarization layer **15** is appropriately performed by a spin-on material having an organic material as a main component. According to this, an unevenness of a base layer is alleviated by the flowability of the spin-on material so that the organic planarization layer **15** having a flat top surface is obtained.

The anti-reflection film **16** and a photoresist film (not illustrated) are sequentially formed on the top surface of the organic planarization layer **15** and the photoresist film is patterned by a photolithographic technology so that first mask layers **17** are obtained. The first mask layers **17** have a line type pattern which extends in one direction. A pattern of the first mask layer **17** is determined in accordance with a pattern of a trench (i.e., an upper layer wiring to be formed later) which will be described below.

Subsequently, a wafer W having a structure illustrated in FIG. 8A is carried into a chamber **102** of the plasma etching device **100**. The anti-reflection film **16** and the organic planarization layer **15** are removed using the first mask layers **17**. The removal is performed by exposing the wafer to the oxygen plasma. Next, when the TiN layer **14** is etched using plasma etching, the pattern of the first mask layers **17** is transferred to the TiN layer **14**. Next, when the first mask layers **17** used for the etching and the anti-reflection film **16** and the organic planarization layer **15** remaining below the first mask layers **17** are removed by the oxygen plasma, metal hard masks (MHMs) **14a** is obtained (S12 of FIG. 7).

Next, an organic planarization layer **25** is formed to cover the MHM **14a** and the silicon oxide film **13** which is a base layer thereof. The organic planarization layer **25** may be formed of the same material and by the same method as the organic planarization layer **15**. Next, an anti-reflection film **26** and a photoresist film are formed on the organic planarization layer **25** and the photoresist film is patterned so that a photoresist mask **27** is formed (S13 of FIG. 7). The photoresist mask **27** has an opening **27h** whose top side shape is substantially rectangular and width is narrower than an interval (an interval of MHMs **14a**) of the first mask layers **17**. Further, the opening **27h** is formed at a position where a via electrically connected with the wiring layer **10** is to be formed and the width of the opening **27h** corresponds to the size of the via.

Next, the anti-reflection film **26** and the organic planarization layer **25** are etched using the photoresist mask **27** as a

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mask and as illustrated in FIG. 8D, a second mask layer **25a** is formed from the organic planarization layer **25** (S14 of FIG. 7). The second mask layer **25a** has an opening **25h** having the same size as the opening **27h** of the photoresist mask **27**.

Next, when the silicon oxide film **13** and the low-k film **12** are subjected to plasma etching by a $C_4F_8/Ar/N_2/O_2$ mixture gas using the second mask layer **25a** and the second mask layer **25a** used for the plasma etching is removed, a structure illustrated in FIG. 8E is obtained (S15 of FIG. 7). In this structure, a hole **t** which passes through the silicon oxide film **13** and has a depth which is smaller than the total thicknesses of the silicon oxide film **13** and the low-k film **12** is formed. Further, the depth of the hole **t** is determined by an etching time.

Next, when the silicon oxide film **13** and the low-k film **12** are subjected to plasma etching again by a $CHF_3/Ar/N_2$ mixture gas using the MHM **14a** as a mask, a structure illustrated in FIG. 8F is obtained (S16 of FIG. 7). Specifically, the plasma etching is performed from a portion (see FIG. 8E) of the silicon oxide film **13** which is not covered by the MHM **14a**, and a trench **T** which reaches a predetermined depth position of the low-k film **12** through the silicon oxide film **13** is formed. In the meantime, the bottom of the hole **t** illustrated in FIG. 8E is also subjected to plasma etching and a via **V** is formed in which the top surface of the wiring layer **10** is formed as the bottom surface of the via **V**. Therefore, a trench/via **TV** is formed. In an illustrated example, the trench **T** has a width of the first mask layer **17** and extends in a direction perpendicular to the width and the via **V** is formed as an opening having a substantially columnar shape at a predetermined position of the bottom of the trench **T**.

Next, a metal is filled in the via **V** and the trench **T** through a damascene process such that a via plug electrically connected to the wiring layer **10** and a metal wiring integrally connected to the via are formed.

Specific Example

Wafer in-plane etching rates were researched in connection with a case in which an oxygen flow rate at a peripheral edge portion of a wafer is changed, a case in which CH_3F gas is introduced into a peripheral edge portion of a wafer, and a case in which C_4F_6 gas is introduced into a peripheral edge portion of a wafer, using the plasma etching device illustrated in FIG. 4. FIG. 9A illustrates etching rates when oxygen flow rates at the peripheral edge portions of wafers are changed, FIG. 9B illustrates etching rates when CH_3F gas is introduced into the peripheral edge portions of wafers, and FIG. 9C illustrates etching rates when C_4F_6 gas is introduced into the peripheral edge portions of wafers.

As illustrated in FIG. 9A, when the O_2 gas introduced into the peripheral edge portion of a wafer was zero, the sudden increase of the etching rate at the peripheral edge portion of the wafer still remains. Further, as illustrated in FIG. 9B, when the CH_3F gas was introduced into the wafer peripheral edge portion, relatively good in-plane uniformity was obtained when the flow rate is 40 sccm. However, the etching rate over the wafer was lowered and the sudden increase of the etching rate at the wafer peripheral edge portion remains slightly. Further, as illustrated in FIG. 9C, when the C_4F_6 gas was introduced into the wafer peripheral edge portion, a satisfactory in-plane uniformity was obtained when a flow rate was 5 sccm.

It is believed that the results of the CH_3F gas and the C_4F_6 gas are different from each other due to the difference of chemical bonds. That is, C_4F_6 is unsaturated (having double bonds of $C=C$), and, thus has a structure that may scavenge

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oxygen radicals more easily. That is, it is believed that a gas containing carbons of an unsaturated structure such as $C_xH_yF_z$, C_xF_y , or C_xH_y (x , y , and z are natural numbers, the same hereinafter) is appropriate.

In addition, in terms of the CH_3F gas and the C_4F_6 gas, it is believed that, since the former has a smaller molecular weight and the introduced flow rate of the former becomes higher, the former is more easily spread widely over the wafer as compared with the C_4F_6 . That is, it is desirable to select a processing gas which has a large molecular weight and, thus, hardly spreads.

Modified Embodiment 1 of Plasma Etching Device

Next, a modified embodiment of the plasma etching device according to the exemplary embodiment will be described. In this modified embodiment, a configuration in the vicinity of the shower head of the plasma etching device illustrated in FIG. 4 is changed. In the following description, the same components as those of the plasma etching device illustrated in FIG. 4 will be denoted by the same reference numerals and overlapping descriptions will be omitted.

As illustrated in FIG. 10A, in a plasma etching device according to the modified embodiment, the shower head **140** (upper electrode **120**) of the plasma etching device illustrated in FIG. 4 is provided to extend beyond the outer circumference of the focus ring **119** to the outside and buffer chambers **143e** to **143g** are provided in addition to the buffer chambers **143a** to **143d**. Pipes **174** to **176** are connected to the buffer chambers **143e** to **143g**, respectively. The pipes **174** to **176** are connected to a gas supplying device (not illustrated) and also allow gases of various flow rate/gas species to be supplied, similarly to the pipes **170** to **173**.

That is, as illustrated in FIG. 10B, the processing gas which has passed through the buffer chambers **143e** to **143g** is adapted to reach the areas **e** to **g** in the peripheral edge area of the wafer **W** so that the etching rate at the peripheral edge portion of the wafer **W** may be controlled. According to the plasma etching device of the present modified embodiment, the etching rate may be uniformized from the central portion to the peripheral edge portion of the wafer and the etched shapes may also be uniformized. Here, the etched shape may be any of an etching rate, in-plane uniformity, and bowing which may be used to determine the quality of a device processing.

Modified Embodiment of Etching Method

Next, a modified embodiment of the plasma etching method according to the exemplary embodiment will be described. In the present modified embodiment, prior to plasma etching, a dummy wafer is carried in and a deposition processing is performed on a focus ring in advance.

First, the device controller **190** opens the gate valve **132**, carries a dummy wafer into the chamber **102**, and dispose the dummy wafer on the electrostatic chuck **111** (S21). After the dummy wafer is carried in, the gate valve **132** is closed and decompression is preformed by the exhausting device **135**.

Next, the gas supplying device **150** introduces a deposition gas (sedimentary gas) such as, for example, $C_xH_yF_z$, C_xF_y , or C_xH_y , into the chamber **102** (S22). The device controller **190** controls the first radio frequency power source **114** or the second radio frequency power source **116** to generate plasma in the chamber **102** so as to perform a deposition processing (S23). In this case, the gas supplying device **150** may supply the deposition gas only to the buffer chamber **143d** and the deposition processing may be intensively performed on the

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peripheral edge portion of the wafer W. A deposition material is deposited on the focus ring 119 by the deposition processing.

Next, the dummy wafer is carried out through the gate valve 132 (S24) and a wafer W to be processed is disposed on the electrostatic chuck 111 (S25). After the wafer W to be processed is carried in, the gate valve 132 is closed and decompression is performed by the exhausting device 135. Next, a predetermined plasma etching process is performed (S26).

According to the present modified embodiment, prior to the plasma etching, since the deposition processing is performed on the focus ring 119 using the deposition gas such as $C_xH_yF_z$, or C_xF_y , or C_xH_y , surplus O radicals on the focus ring may be removed in the plasma etching process.

Modified Embodiment 2 of Plasma Etching Device

Next, a modified embodiment of the plasma etching device according to the embodiment will be described. In the present modified embodiment, a configuration in the vicinity of the shower head and a configuration in the vicinity of the focus ring of the plasma etching device illustrated in FIG. 4 are modified. In the following description, the same components as those of the plasma etching device illustrated in FIG. 4 are denoted by the same reference numerals and overlapping descriptions will be omitted.

As illustrated in FIG. 12A, the plasma etching device according to the modified embodiment includes a support 104a which adjusts the temperature of the focus ring 119 of the plasma etching device illustrated in FIG. 4, an electrostatic electrode 119a which generates plasma above the focus ring 119, a radio frequency power source 114a, a matching unit 115a, and an inductively coupled plasma device (ICP device) 140a which is provided at an outer peripheral portion of the shower head 140. That is, in the present modified embodiment, a mechanism configured to generate the plasma above the focus ring 119 is added to the plasma etching device illustrated in FIG. 4.

Next, the operation of the plasma etching device according to the present modified embodiment will be described with reference to FIG. 12B. After a wafer to be processed is carried onto the electrostatic chuck 111, the gas supplying device 150 introduces a deposition gas such as $C_xH_yF_z$, C_xF_y , or C_xH_y into the peripheral edge portion of the wafer (or on the focus ring) (S31). Further, the support 104a lowers the temperature of the focus ring 119 and increases a radical adsorption rate on the focus ring 119 (S32).

Next, the device controller 190 connects the radio frequency power source 114a to the electrostatic electrode 119 to apply a radio frequency voltage and generate plasma (S33). The plasma on the focus ring 119 may be generated using the radio frequency voltage applied by the radio frequency power source 114a, using an ICP device 140a, or using both the radio frequency power source 114a and the ICP device 140a. Further, the same effects may also be obtained when the focus ring is cooled in the conventional plasma etching, rather than generating the plasma on the focus ring 119.

According to the present modified embodiment, since the plasma is generated on the focus ring using the deposition gas to perform the deposition processing, surplus O radicals may be removed from the focus ring in the plasma etching processing.

Although the exemplary embodiments of the present disclosure have been described above, the present disclosure is not limited to the specific embodiments and various modifications or changes may be made within the scope of the

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present disclosure described in the following claims. For example, a workpiece capable of being etched in the plasma etching device 100 according to the exemplary embodiments of the present disclosure is not particularly limited. For example, as a wafer including a silicon substrate, a wafer which is formed with a silicon dioxide (SiO_2) film, a film to be etched including a polysilicon film, a mask layer formed in a single layer or multiple layers, an anti-reflection film (bottom anti-reflective coating (BARC)), and a photoresist film thereon may be used.

REFERENCE NUMERALS

W: Wafer

105: Susceptor (support unit)

106: Temperature distribution adjusting unit

120: Upper electrode (electrode)

122: Bellows

130: Gas supplying condition adjusting unit

140: Shower head

143: Buffer chamber

145: Annular partitioning member

150: Gas supplying device

190: Device controller

200: Upper electrode driving unit

The invention claimed is:

1. A method of manufacturing a semiconductor device including a wafer using a plasma etching device which includes a chamber, a chuck provided in the chamber to dispose the wafer to be processed thereon, a focus ring disposed at a peripheral edge portion of the chuck to surround the wafer disposed on the chuck, and a gas supplying mechanism configured to separately supply various types of gases, the method comprising:

providing a shower head having a plurality of regions including a central region and a peripheral edge region surrounding the central region, each region configured to selectively supply one of the various types of gases from the gas supplying mechanism to each of a plurality of regions of the wafer along a radial direction of the wafer;

placing a wafer covered with an organic film on the chuck; introducing, from the gas supplying mechanism through the central region of the shower head to a central portion of the wafer, an etching gas which includes at least O_2 gas and etches the organic film on the wafer;

introducing, from the gas supply mechanism through the peripheral edge region of the shower head to a peripheral edge portion of the wafer, an etching inhibiting factor gas having a property of reacting with O radicals which do not react with the organic film and exists on the focus ring when a plasma etching is performed; and

performing the plasma etching on the wafer using the etching gas by generating plasma with the etching gas while eliminating the O radicals and thereby suppressing etching in the peripheral edge portion of the wafer, wherein the etching inhibitor gas includes at least a C_xF_y gas.

2. The method of claim 1, wherein the etching inhibiting factor gas is formed of a gas which includes at least one of CF_4 , C_4F_6 , and C_4F_8 .

3. The method of claim 1, wherein the etching inhibiting factor gas is formed of a gas which includes at least a C_4F_6 gas.

4. The method of claim 1, wherein the etching inhibiting factor gas is formed of a mixture gas which includes an unsaturated gas.

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5. The method of manufacturing a semiconductor device of claim 1, wherein each of the plurality of regions of the shower head is separated by an O ring.

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